



**TSMBJ0505C
 thru
 TSMBJ0527C**

Features

- Bidirectional Transient Voltage Protection
- Surge Capabilities up to 50 Amps @ 10/1000µs or 200 Amps @ 8/20µs (note 2, 5)
- Initial Breakdown Voltages from 60 to 335 Volts
- Positive Resistance Breakover Voltages from 100 to 440 Volts
- Clamping Speeds of Nanoseconds
- Oxide-Glass Passivated Junctions
- High Off-State Impedance (low leakage) and Low On-State Voltage (crowbar action)
- Encapsulating material meets UL94VO Requirements
- UL497B Recognized/UL File No. E152273
- ISO 9001 Certified

Maximum Ratings

- Operating Temperature: -40°C to + 150°C (note 5)
- Storage Temperature: -65°C to + 150°C
- Repetitive Off-State Voltage (both directions): See Electrical Characteristics for V_{DRM}
- Non-Repetitive Peak Impulse Current (I_{PPS}): 50 A @ 10/1000µs or 200 A @ 8/20µs (note 5)
- Non-Repetitive Peak On-State Current (I_{TSM}) @ 8.3ms (one-half cycle): 30 Amps

Electrical Characteristics @ 25°C Unless otherwise specified

Rated Peak Impulse Current 50 Amps @ 10/1000ms (see note 6)	Rated Repetitive Off-State Voltage (see note 3)	Off-State Leakage Current @ V _{DRM}	Breakdown Voltage @ I _(BR) = 1mA (see note 4)	Breakover Voltage (see note 1)	On-State Voltage @ I _T = 1A (pulse)	Holding Current		Capacitance (1MHz)	
						I _H mA	I _H mA	C _o @ 0v pF	C _o @ 50v pF
Part Numbers (see note 6)	V _{DRM} Volts	I _{DRM} mA	V _(BR) Volts	V _(BO) Volts	V _T Volts	I _H MIN.	I _H MAX.	C _o MAX.	C _o MAX.
TSMBJ0505C	50	5	60	100	4.0	150	750	200	100
TSMBJ0506C	60	5	70	110	4.0	150	750	200	100
TSMBJ0507C	70	5	85	145	4.0	150	750	200	100
TSMBJ0509C	90	5	115	185	4.0	150	750	200	100
TSMBJ0510C	100	5	125	200	4.0	150	750	200	100
TSMBJ0511C	110	5	135	210	4.0	150	750	200	100
TSMBJ0512C	120	5	150	215	4.0	150	750	200	100
TSMBJ0514C	140	5	175	250	4.0	150	750	200	100
TSMBJ0516C	160	5	190	265	4.0	150	750	200	100
TSMBJ0518C	180	5	220	300	4.0	150	750	200	100
TSMBJ0522C	220	5	275	350	4.0	150	750	200	100
TSMBJ0524C	240	5	300	400	4.0	150	750	200	100
TSMBJ0527C	270	5	335	440	4.0	150	750	200	100

Consult factory for additional voltage and holding current tolerance options.

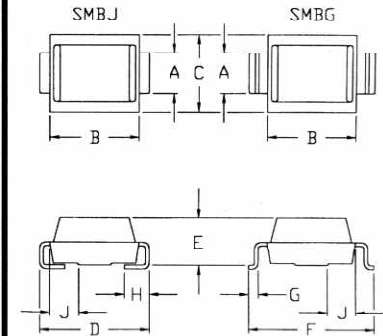
Notes:

- For rise times less than 1 kV/ms. For very fast rise times up to 1 kV/µs, V_(BO) will be 110% of V_(BO) Max., The Max. I_(BO) is 750mA.
- Critical rate of rise of on-state current is 100A/µs Max.
- Maximum rate of rise of off-state voltage V_{DRM} that will not trigger device is 5kV/µs (T_J=70°C).
- Breakdown voltage V_(BR) has a positive temperature coefficient of +0.1%/°C.
- Above 70°C, derate linearly to zero @ 150°C lead temperature.
- For different packages or die options replace part number prefix as follows:
 TSMBJ for surface mount DO-214AA with J-bend (as shown)
 TSMBG for surface mount DO-215AA with Gull Wing
 TSH for DO-13 hermetic axial lead metal package
 TSF for T-18 axial lead plastic
 TSEP for Case 1 axial, 0.040" diameter leads
 TSES for Case 2 axial, 0.030" diameter leads
 TCD for cellular die package
 TCH for chip equivalent in hybrid applications

**Bi-Directional
 50 Amp
 50-270 Volts
 Thyristor Surge
 Protective Device
 (TSPD)**

MECHANICAL CHARACTERISTICS

CASE STYLE: SMBJ (DO-214AA) and SMBG (DO-215AA)



	INCHES MIN/MAX	MILLIMETERS MIN/MAX
A	.077/.083	1.96/2.10
B	.160/.180	4.06/4.57
C	.130/.155	3.30/3.94
D	.205/.220	5.21/5.59
E	.075/.095	1.91/2.41
F	.235/.255	5.97/6.48
G	.015/.030	0.38/0.76
H	.030/.060	0.76/1.52
J	.038/.058	0.97/1.47

ADDITIONAL PACKAGE STYLES:

For other package styles contact Microsemi Scottsdale's TSPD Group for detail package dimensions.

LEAD FINISH: Solder Dip or Lead Tin Plate

POLARITY: Bi-directional